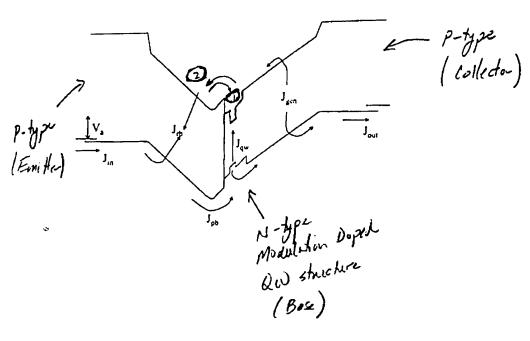


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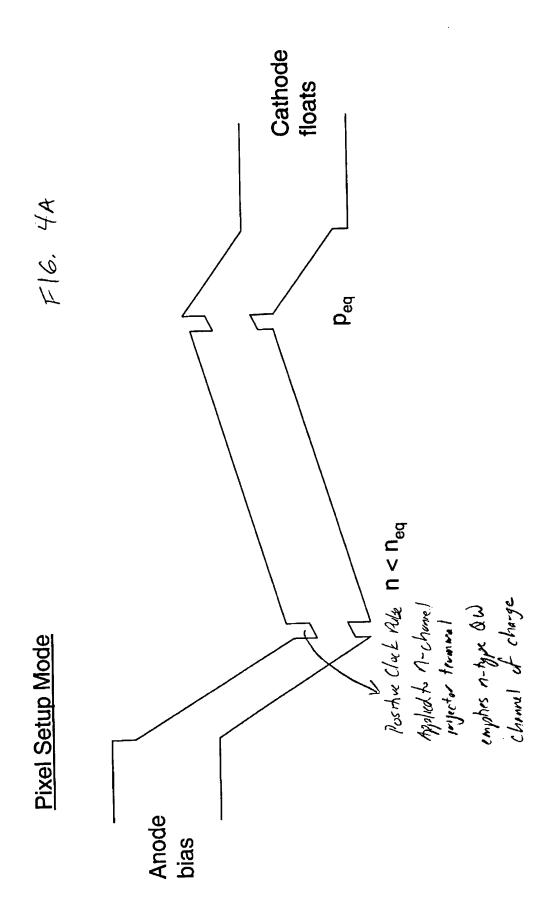
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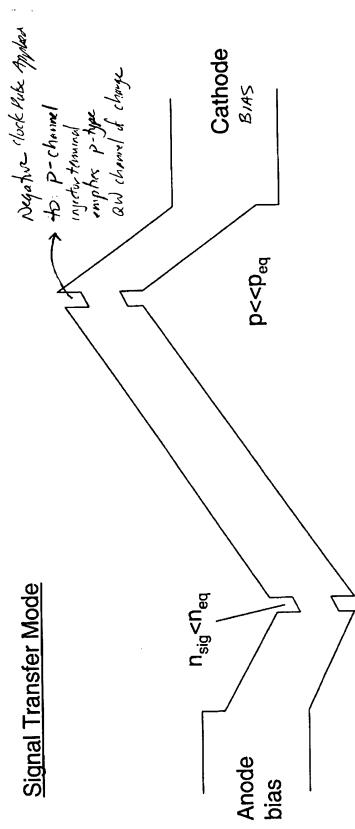
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FIG. 3B

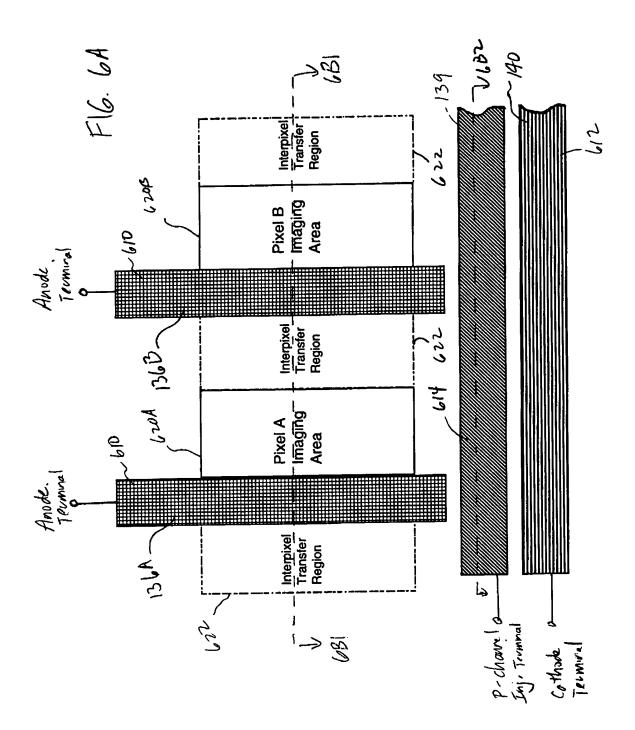


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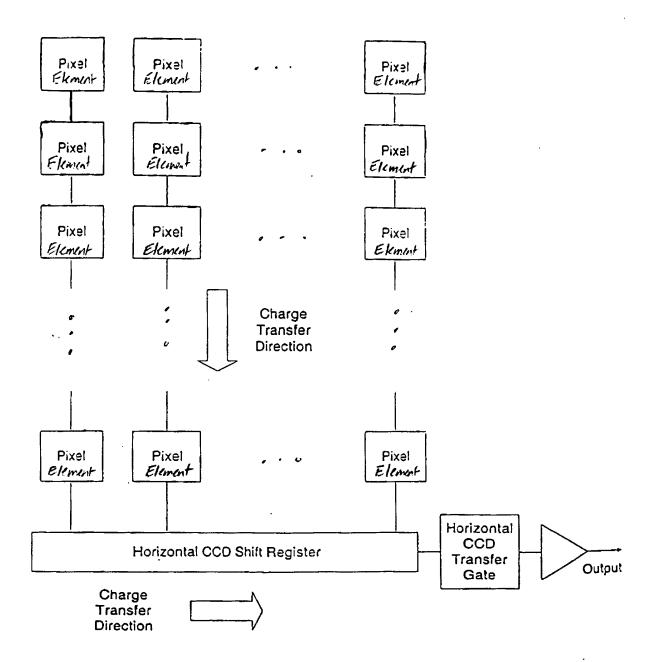
	Layer <b>Mate</b> riai	Layer Doping Type	Typical Doping Concentration (atoms/cm <sup>3</sup> )	Typical Layer Thickness (A)	Layer#
$^{\prime}$	inGaAs	P+	1E20	25	1165b
<b>\</b>		P+	1E20	75	1165a
<b>/</b>	GaAs	P	1E17	700	I164b
1 }	AI(0.7)Ga(0.3)As	P+	1E19	10	1164a
1	AI(0.7)Ga(0.3)As	P+	3.5E18	25	1163d
2	AI(.15)Ga(.85)As	und	und	200 - 300	1163c
거	Al(.15)Ga(.85)As	N+	3.5E18	80	/163b
1	AI(.15)Ga(.85)As	und	und	20-30	/163a
1	AI(.15)Ga(.85)As	und	und	15	1162
<b>ا</b> ک	GaAs	und	und	60	1161
	In(.20)Ga(.80)AsN)	und	und	100	1160b
1	GaAs Jry	und	und	100 - 250	1160a
		und	und	5000	1159
	AI(.15)Ga(.85)As	บกป	und	100	1158
$\Big)\Big $	In(.20)Ga(.80)AsN	und	und	60	1157
		und	und	15	1156
5	GaAs	und	und	30	1155d
( )	AI(.15)Ga(.85)As	P+	3.5E18	80	(155c
ζ	AI(.15)Ga(.85)As AI(.15)Ga(.85)As	und	und	300	1155b
7	Al(.15)Ga(.85)As	N+	3.5E18	80	ı1 <u>55a</u>
- }	Al(0.7)Ga(0.3)As	N	1E17	700	1154
1	GaAs	N+	3.5E18	2200	1153
7	AlAs	und	und	1701	1151
Į	Gang X X 3	1		696	1152
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{	GaAs X 7 AlAs GaAs Substrate	und und	und und SI		

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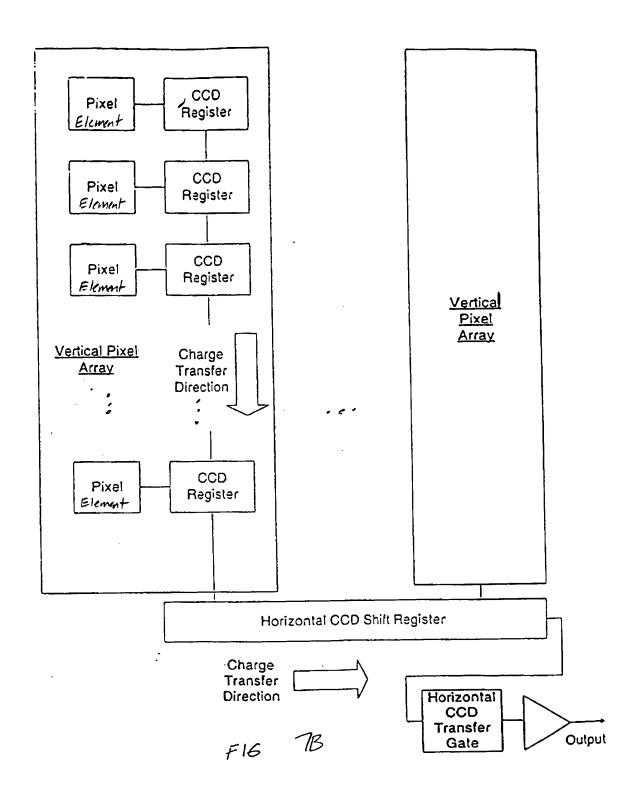


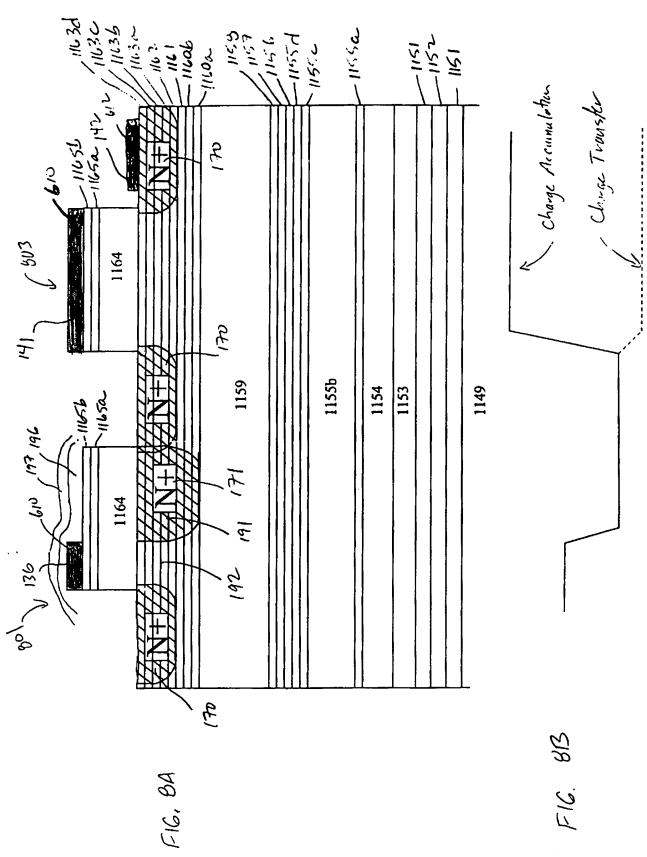
153 1154 1156 1155 1155 1811 -~1155m 139 261 1155b 1149 1154 (153

F16. 6B2



F16. 7A





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